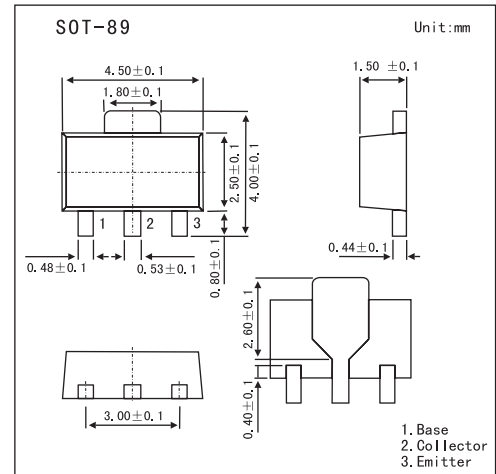


Epitaxial Planar PNP Transistor

KTA1660

■ Features

- High Voltage: $V_{CE0}=-150V$
- High Transition Frequency: $f_T=120MHz$
- Small Flat Package

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	-150	V
Collector-Emitter Voltage	V_{CE0}	-150	V
Emitter-Base Voltage	V_{EB0}	-5	V
Collector Current	I_C	-50	mA
Base Current	I_B	-10	mA
Collector Power Dissipation	P_C	500	mW
	P_{C^*}	1	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 to 150	$^\circ C$

* mounted on ceramic substrate ($250mm^2 \times 0.8t$)

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector Cut-off Current	I_{CBO}	$V_{CB}=-150V, I_E=0$			-0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{CE}=-5V, I_C=0$			-0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=-5V, I_C=-10mA$	70		240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-10mA, I_B=-1mA$			-0.8	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=-5V, I_C=-30mA$			-0.9	V
Transition Frequency	f_T	$V_{CE}=-30V, I_C=-10mA$		120		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		4.0	5.0	pF

■ h_{FE} Classification

Marking	BO	BY
Rank	O	Y
Type	70~140	120~240